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# BLC8G27LS-100AV

# **Power LDMOS transistor**

**AMPLEON** 

Rev. 4 — 2 December 2016

Product data sheet

## 1. Product profile

#### 1.1 General description

100 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2496 MHz to 2690 MHz.

#### Table 1. Typical performance

Typical RF performance at  $T_{case}$  = 25 °C in the Doherty demo board.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	Gp	η <sub>D</sub>	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2520 to 2620	28	18	15.5	45	-30 <u>[1]</u>

<sup>[1]</sup> Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

 RF power amplifier for LTE base stations and multi carrier applications in the 2496 MHz to 2690 MHz frequency range

#### **Pinning information** 2.

Table 2. **Pinning** 

Pin	Description		Simplified outline	Graphic symbol
1	drain1 (main)			
2	drain2 (peak)			1, 5
3	gate1 (main)			3_
4	gate2 (peak)		7	7
5	video decoupling (main)			4 4
6	video decoupling (peak)		3 4	2, 6
7	source	[1]		aaa-007731

<sup>[1]</sup> Connected to flange.

#### **Ordering information** 3.

**Ordering information** Table 3.

Type number	Packag	ckage						
	Name	Description	Version					
BLC8G27LS-100AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1					

#### **Limiting values** 4.

Table 4. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

#### **Thermal characteristics** 5.

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from junction to case	$T_{case}$ = 80 °C; $V_{DS}$ = 28 V; $I_{Dq}$ = 250 mA		
		P <sub>L</sub> = 18 W	0.314	K/W
		P <sub>L</sub> = 65 W	0.289	K/W

#### 6. Characteristics

Table 6. DC characteristics

 $T_i$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	rain-source breakdown voltage $V_{GS} = 0 \text{ V}; I_D = 0.51 \text{ mA}$		-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS}$ = 10 V; $I_{D}$ = 51 mA	1.5	1.9	2.3	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS}$ = 28 V; $I_{D}$ = 306 mA	1.7	2.0	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	9.6	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nΑ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 51 mA	-	0.46	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.785 \text{ A}$	-	294	451	mΩ
Peak dev	rice			1		
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.72 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS}$ = 10 V; $I_{D}$ = 72 mA	1.5	1.9	2.3	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS}$ = 28 V; $I_{D}$ = 432 mA	1.7	2.0	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	13.4	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 72 mA	-	0.62	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 2.52 \text{ A}$	-	210	323	mΩ

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH;  $f_1$  = 2496 MHz;  $f_2$  = 2690 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 250 mA (main);  $V_{GS(amp)peak}$  = 0.8 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L(AV)</sub> = 17.8 W	14.3	15.5	-	dB
RLin	input return loss	P <sub>L(AV)</sub> = 17.8 W	-	-10	<b>-6</b>	dB
$\eta_{D}$	drain efficiency	P <sub>L(AV)</sub> = 17.8 W	39	44	-	%
ACPR	adjacent channel power ratio	P <sub>L(AV)</sub> = 17.8 W	-	-31	-25	dBc

#### Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f = 2690 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 250 mA (main);  $V_{GS(amp)peak}$  = 0.8 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PARO	output peak-to-average ratio	P <sub>L(AV)</sub> = 50 W	3.6	4.2	-	dB
$P_{L(M)}$	peak output power		112	133	-	W

BLC8G27LS-100AV

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### 7. Test information

#### 7.1 Ruggedness in Doherty operation

The BLC8G27LS-100AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 28 V;  $I_{Dq}$  = 250 mA (main);  $V_{GS(amp)peak}$  = 0.8 V;  $P_L$  = 70 W (CW); f = 2496 MHz.

### 7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device;  $I_{Dq} = 300 \text{ mA (main)}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum pov	Maximum power load									
2496	2.5 – j6.7	4.0 – j7.6	63	56.0	16.0					
2600	3.4 – j7.0	4.0 – j7.6	61	55.6	16.7					
2690	3.2 – j6.2	4.0 – j7.6	60	56.1	17.1					
Maximum dra	in efficiency load									
2496	2.5 – j6.7	7.1 – j5.1	47.9	64	18.2					
2600	3.4 – j7.0	6.5 – j4.6	44.3	63	19.0					
2690	3.2 – j6.2	6.0 – j4.1	40.5	62	19.5					

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device;  $I_{Dq}$  = 400 mA (main);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum po	Maximum power load									
2496	2.6 – j6.4	2.7 – j7.1	83	55.7	17.8					
2600	3.2 – j6.9	2.1 – j7.1	82	51.4	17.7					
2690	4.3 – j7.8	2.1 – j7.1	82	53.2	18.4					
Maximum dra	ain efficiency load									
2496	2.6 – j6.4	4.0 – j5.6	61	66.6	19.7					
2600	3.2 – j6.9	3.7 – j5.1	62	60.8	20.1					
2690	4.3 – j7.8	3.3 – j5.4	61	60.5	20.6					

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in <u>Figure 1</u>.

<sup>[2]</sup> at 3 dB gain compression.

<sup>[2]</sup> at 3 dB gain compression.

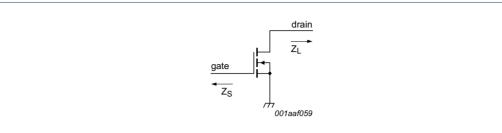


Fig 1. Definition of transistor impedance

### 7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load Measured load-pull data of main device;  $I_{Dq} = 300 \text{ mA (main)}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2496	2.5 – j6.7	5.1 – j6.5	59	36.8	20.0
2600	3.4 – j7.0	5.1 – j6.5	56	38.0	20.5
2690	3.2 – j6.2	5.1 – j6.5	56	39.2	21.2

- [1] Z<sub>S</sub> and Z<sub>L</sub> defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at  $P_{L(AV)} = 42.5 \text{ dBm}$ .

Table 12. Typical impedance of main device at 1 : 2.5 load

Measured load-pull data of main device;  $I_{Dq}$  = 300 mA (main);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2496	2.5 – j6.7	11.2 – j2.7	31	52.0	22.2
2600	3.4 – j7.0	10.0 – j2.3	30	51.1	22.5
2690	3.2 – j6.2	7.5 – j0.8	25	52.2	22.1

- [1]  $Z_S$  and  $Z_L$  defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at  $P_{L(AV)} = 42.5 \text{ dBm}$ .

### 7.4 VBW in Doherty operation

The BLC8G27LS-100AV shows 130 MHz (typical) video bandwidth in Doherty demo board in 2600 MHz at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 250 mA and  $V_{GS(amp)peak}$  = 0.8 V.

#### 7.5 Test circuit

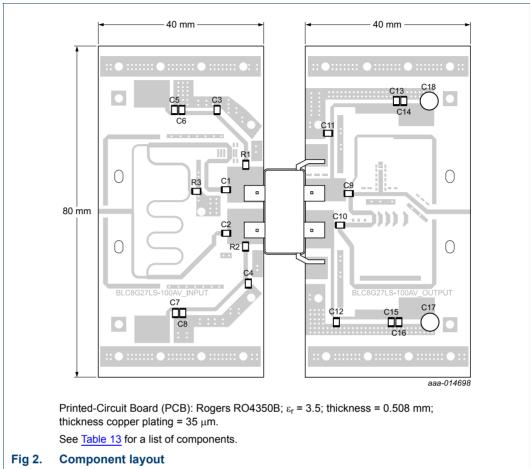


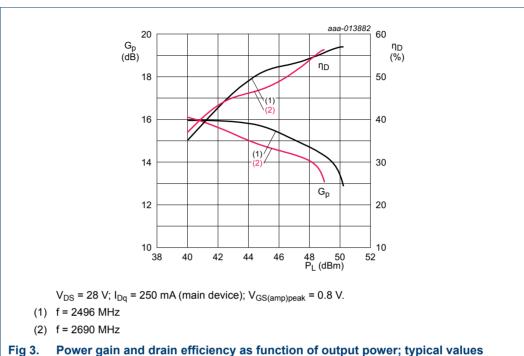
Table 13. List of components See Figure 2 for component layout.

Component	<b>Description</b> Value		Remarks
C1, C2, C3, C4, C10, C11, C12	multilayer ceramic chip capacitor	11 pF [1]	ATC 600F
C9	multilayer ceramic chip capacitor	5.1 pF [1]	ATC 600F
C6, C8, C13, C15	multilayer ceramic chip capacitor	1 μF, 50 V [2]	Murata
C5, C7, C14, C16	multilayer ceramic chip capacitor	10 μF, 50 V [2]	Murata
C17, C18	electrolytic capacitor	470 μF, 50 V	
R1, R2	SMD resistor	9.1 Ω	SMD 0805
R3	SMD resistor	50 Ω	SMD 0805

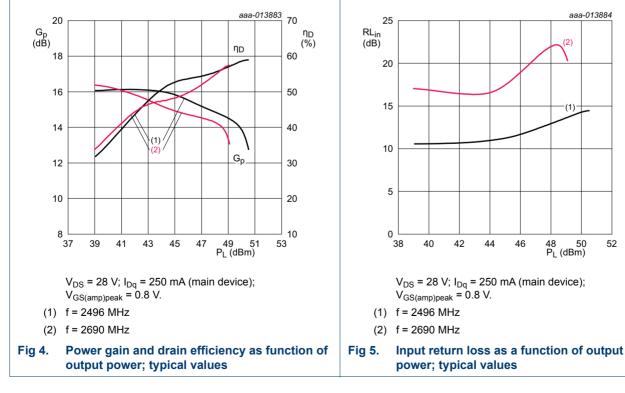
- [1] American Technical Ceramics type 600F or capacitor of same quality
- Murata or capacitor of same quality

### 7.6 Graphical data

#### 7.6.1 CW

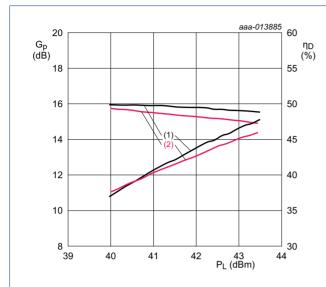


#### 7.6.2 Pulsed CW



52

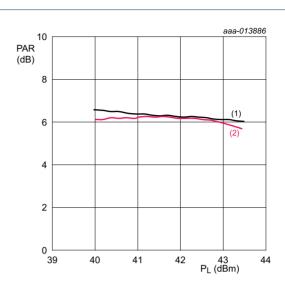
#### 7.6.3 1-Carrier W-CDMA



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.8 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

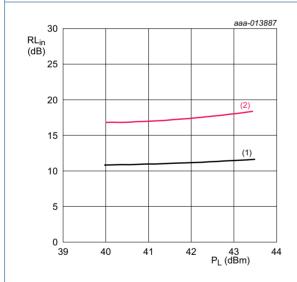
Fig 6. Power gain and drain efficiency as function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.8 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

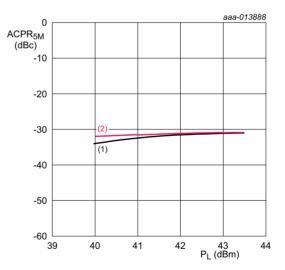
Fig 7. Peak-to-average power ratio as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.8 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 8. Input return loss as a function of output power; typical values

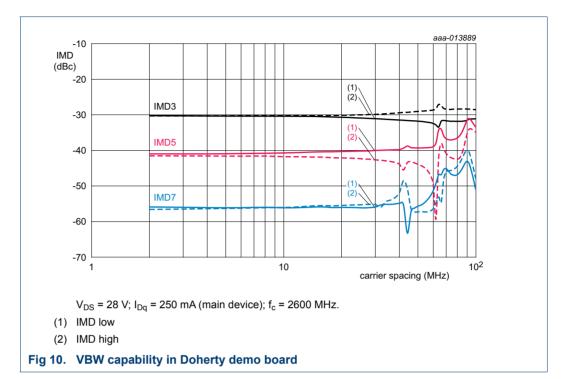


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.8 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 9. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

#### 7.6.4 2-Tone VBW



## 8. Package outline

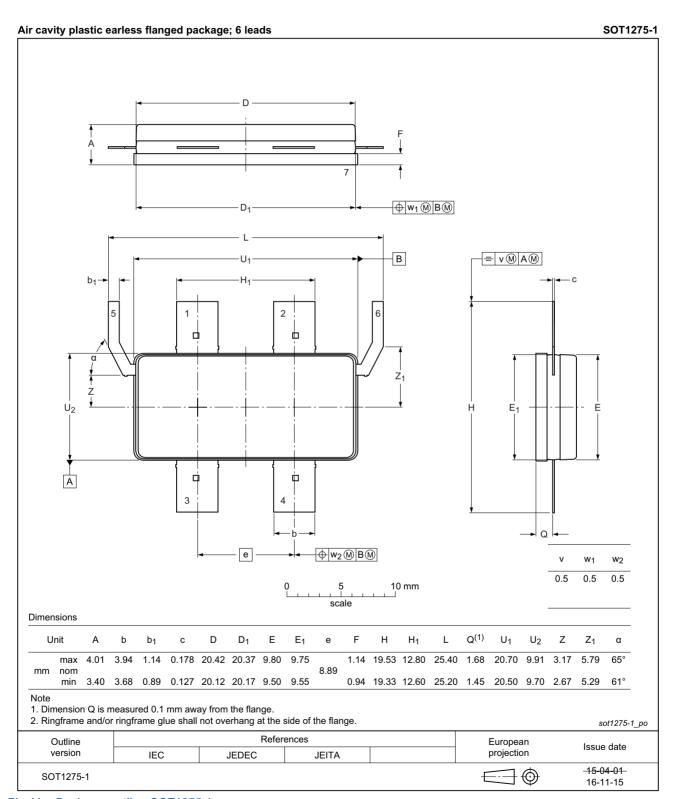


Fig 11. Package outline SOT1275-1

## 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

### 10. Abbreviations

Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LTE	Long Term Evolution
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

## 11. Revision history

#### Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC8G27LS-100AV v.4	20161202	Product data sheet	-	BLC8G27LS-100AV v.3
Modifications:	• Figure 11 on	page 10: updated package	e outline drawing SO	T1275-1
	Section 9 on	page 11: updated Handling	g information	
BLC8G27LS-100AV v.3	20150901	Product data sheet	-	BLC8G27LS-100AV v.2
BLC8G27LS-100AV v.2	20140929	Product data sheet	-	BLC8G27LS-100AV v.1
BLC8G27LS-100AV v.1	20140225	Objective data sheet	-	-

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.ampleon.com">http://www.ampleon.com</a>.

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### 13. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

# **AMPLEON**

# **BLC8G27LS-100AV**

#### **Power LDMOS transistor**

### 14. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information
3	Ordering information
4	Limiting values
5	Thermal characteristics 2
6	Characteristics
7	Test information 4
7.1	Ruggedness in Doherty operation 4
7.2	Impedance information 4
7.3	Recommended impedances for Doherty design 5
7.4	VBW in Doherty operation 5
7.5	Test circuit
7.6	Graphical data 7
7.6.1	CW
7.6.2	Pulsed CW
7.6.3	1-Carrier W-CDMA 8
7.6.4	2-Tone VBW
8	Package outline
9	Handling information 11
10	Abbreviations11
11	Revision history 12
12	Legal information
12.1	Data sheet status
12.2	Definitions
12.3	Disclaimers
12.4	Trademarks14
13	Contact information 14
14	Contents

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